

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

SN74LVC1G14

产品手册

产品简介

SN74LVC1G14 是一款的施密特触发功能的非门集成电路,可实现 $Y = \overline{A}$ 的数学逻辑运算。采用先进 CMOS 工艺设计,具有低功耗和高输出驱动能力的工作特点, 电源电压 VCC 在 1.65V 和 5.5V 之间芯片均可正常工作。并且 SN74LVC1G14 具有多种小型封装外形,可广泛应用于高端精密仪器和小型化低功耗的手持设备,以及人工智能等领域。

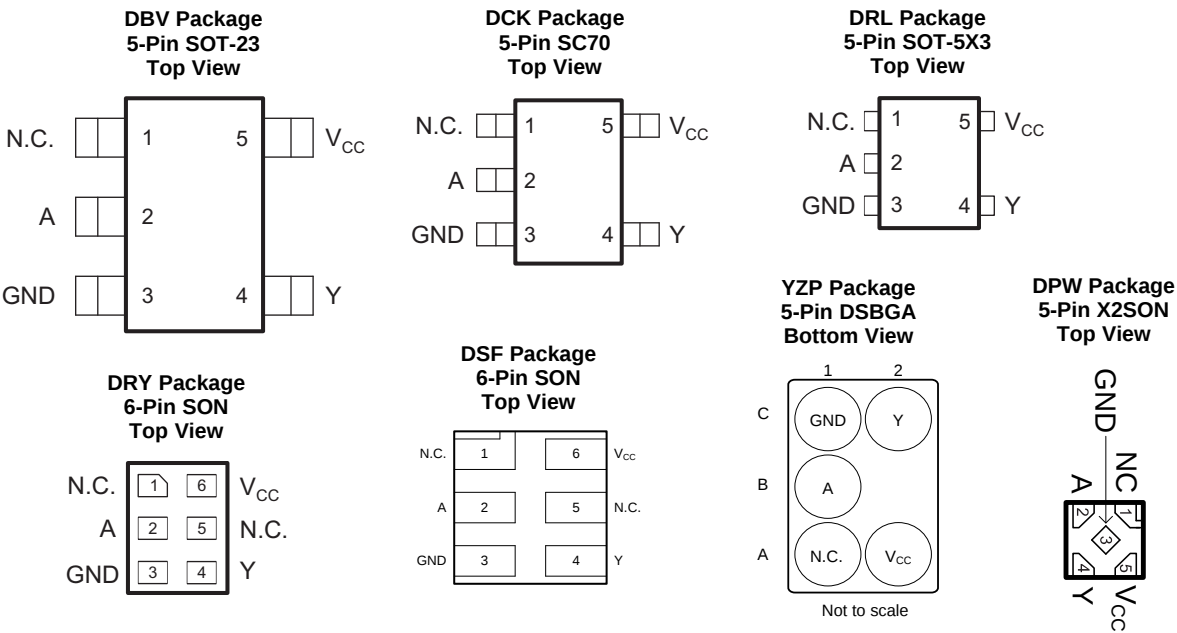
产品特点

- 低输入电流: 典型值 0.1uA
- 低静态功耗: 典型值 0.1uA
- 高输出驱动: VCC=4.5V, 大于 32MA
- 宽工作电压范围: 1.65V to 5.5V
- 封装形式: DBV/DCK/DRL/YZP/ DRY/DSF/ DPW

产品用途

- 便携式音频接口
- 蓝光播放器和家庭影院
- 数字电视
- 固态硬盘
- 无线耳机, 智能手表等
- 智能穿戴设备

引脚配置及功能



See mechanical drawings for dimensions.
N.C. – No internal connection

管脚					
名称	DBV/DCK/DRL	DRY/DSF	YZP	DPW	说明
NC	1	1, 5	A1, B2	1	空脚
A	2	2	B1	2	输入
GND	3	3	C1	3	电源地
Y	4	4	C2	4	输出
VCC	5	6	A2	5	电源正

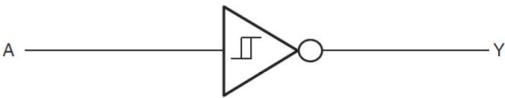
注: NC——空脚, 内部无连接线

极限参数

参数	符号	极限值	单位
工作电压	V_{CC}	6.5	V
输入	V_{IN}	-0.5~6.5	V
输出电压 (1)	V_{OUT}	-0.5~6.5	V
单个管脚输出电流	I_{OUT}	25	mA
V_{CC} 或 GND 电流	I_{CC}	50	mA
存储温度	T_S	-65~150	°C
引脚焊接温度	T_W	260, 10s	°C

注：1、在 $V_{CC}=0V$ 断电状态下，输出所能承受的极限电压，
2、极限参数是指无论在任何条件下都不能超过的极限值。万一超过此极限值，将有可能造成产品劣化等物理性损伤；同时在接近极限参数下，不能保证芯片可以正常工作。

原理逻辑图



真值表

Inputs	Output
A	Y
L	H
H	L

工作条件

项目	符号	测试条件	最小值	典型值	最大值	单位
工作电压	V_{CC}	—	1.65	—	5.5	V
输入高电平电压	V_{IH}	$V_{CC} = 1.65V \sim 1.95V$	$0.65 * V_{CC}$	—	—	V
		$V_{CC} = 2.3V \sim 2.7V$	1.7V	—	—	
		$V_{CC} = 3V \sim 5.5V$	$0.7 * V_{CC}$	—	—	
输入高电平电压	V_{IH}	$V_{CC} = 1.65V \sim 1.95V$	—	—	$0.35 * V_{CC}$	V
		$V_{CC} = 2.3V \sim 2.7V$	—	—	0.7	
		$V_{CC} = 3V \sim 5.5V$	—	—	$0.3 * V_{CC}$	
输入电压	V_I	—	0	—	5.5	V
输出电压	V_O	—	0	—	V_{CC}	V
高电平输出电流	I_{OH}	$V_{CC} = 1.65V$	—	—	-4	mA
		$V_{CC} = 2.3V$	—	—	-8	
		$V_{CC} = 3V$	—	—	-16	
		$V_{CC} = 4.5V$	—	—	-32	
低电平输出电流	I_{OL}	$V_{CC} = 1.65V$	—	—	4	mA
		$V_{CC} = 2.3V$	—	—	8	
		$V_{CC} = 3V$	—	—	16	
		$V_{CC} = 4.5V$	—	—	32	

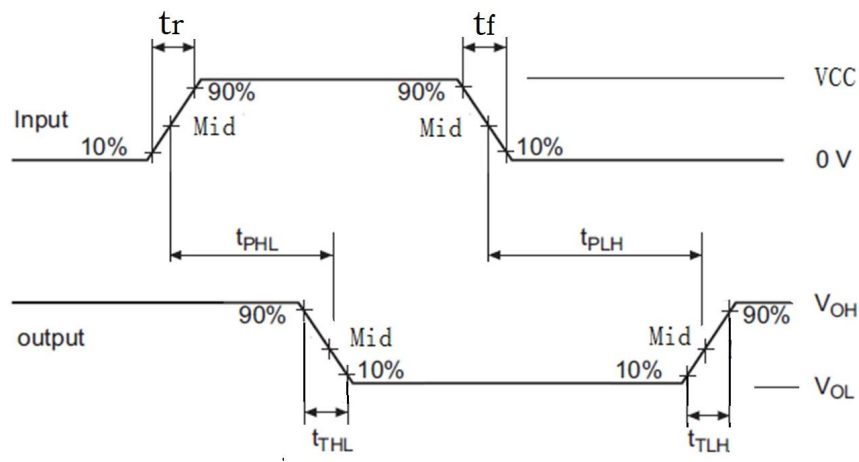
电学特性

直流电学特性：TA=25℃

项目	符号		测试条件	V _{cc}	典型值	最大值	单位
上临界电压	V _{T+}	-	-	1.65V	1	-	V
				2.3V	1.35	-	
				3V	1.7	-	
				4.5V	2.5	-	
				5.5V	3	-	
下临界电压	V _{T-}	-	-	1.65V	0.5	-	V
				2.3V	0.7	-	
				3V	1.1	-	
				4.5V	1.65	-	
				5.5V	1.9	-	
滞后宽度电压	D V _T (V _{T+} - V _{T-})	-	-	1.65V	0.5	-	V
				2.3V	0.65	-	
				3V	0.6	-	
				4.5V	0.85	-	
				5.5V	1.1	-	
高电平负载电压	V _{OH}		I _{OH} =-100uA	1.65V~5.5V	1.64	-	V
			I _{OH} =-4 mA	1.65V	1.47	-	
			I _{OH} =-8 mA	2.3V	2.15	-	
			I _{OH} =-16 mA	3V	2.73	-	
			I _{OH} =-32 mA	4.5V	4.0	-	
低电平负载电压	V _{OL}		I _{OH} =100uA	1.65V~5.5V	0.01	-	V
			I _{OH} =4 mA	1.65V	0.11	-	
			I _{OH} =8 mA	2.3V	0.11	-	
			I _{OH} =16 mA	3V	0.2	-	
			I _{OH} =32 mA	4.5V	0.35	-	
输入电流	I _I	A	V _I =5.5V 或 GND	0~5.5V	0.01	±5	uA
关断电流	I _{OFF}	V _I	V _I =5.5V	0	0.01	±10	uA
		V _O	V _O =5.5V	0	0.01	±10	
工作电流	I _{CC}		V _I =5.5V, I _O =0	1.65V~5.5V	0.01	10	uA
			V _I =GND, I _O =0		0.01	10	
工作电流变化值	ΔI _{CC}		A=V _{CC} -0.6V	3V~5.5V	25	-	uA

交流电学特性: Ta=25℃ VCC=5.0V, tr =tf≤20ns 见测试方法。

项目	符号	测试条件	最小值	典型值	最大值	单位
最大传输延迟时间	tPHL	CL=15pF	-	20	-	ns
A、B to Y	tPLH	CL=15pF	-	20	-	ns

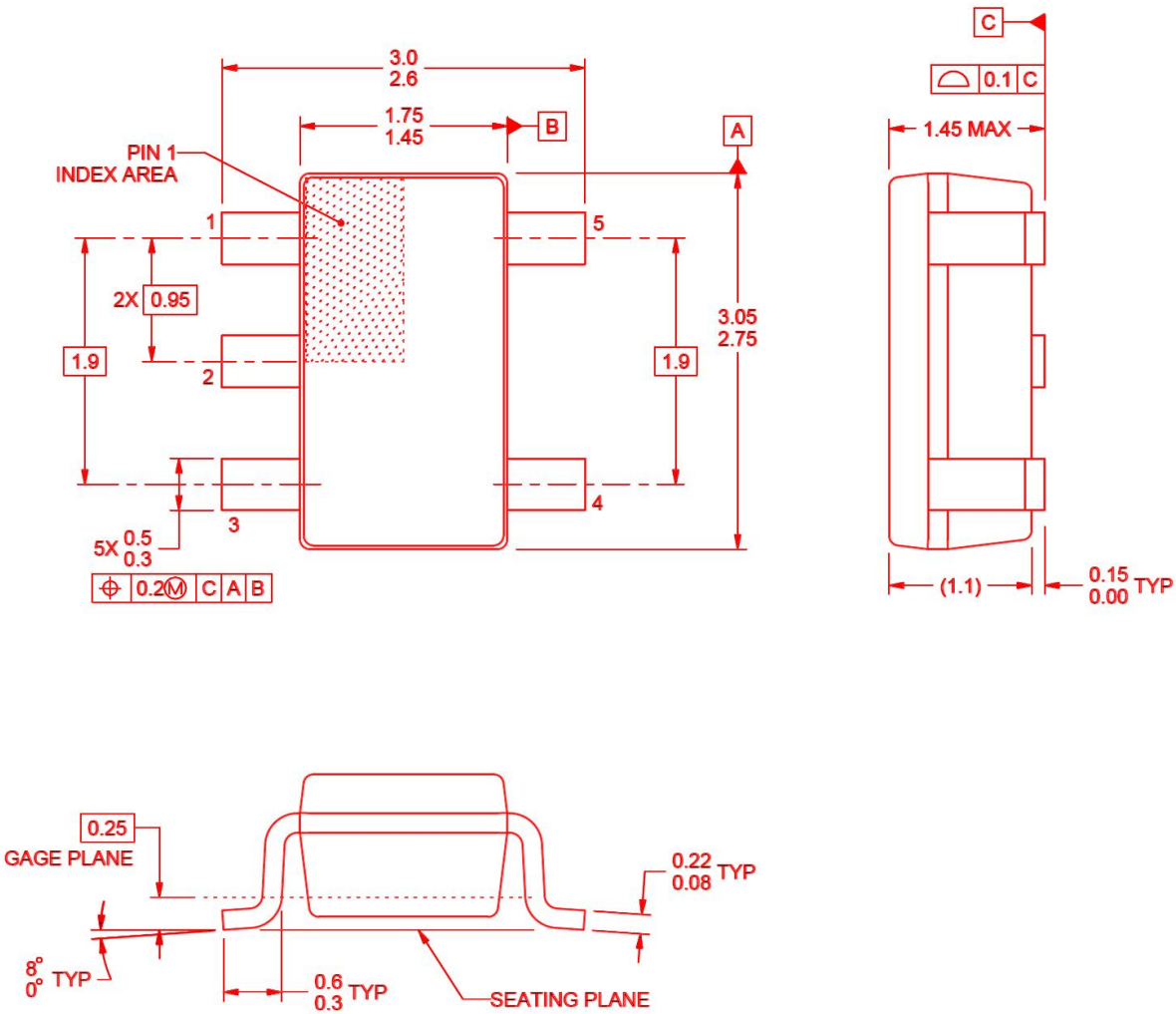


- 注：1、CL电容为外接贴片电容（0603），靠近输出管脚接入，电容地靠近芯片GND；
2、Input：端口输入电平，f=500kHz,D=50%；tr=tf≤20ns；
3、Output：Y 端输出测试。

封装信息

单位：毫米 / 英寸

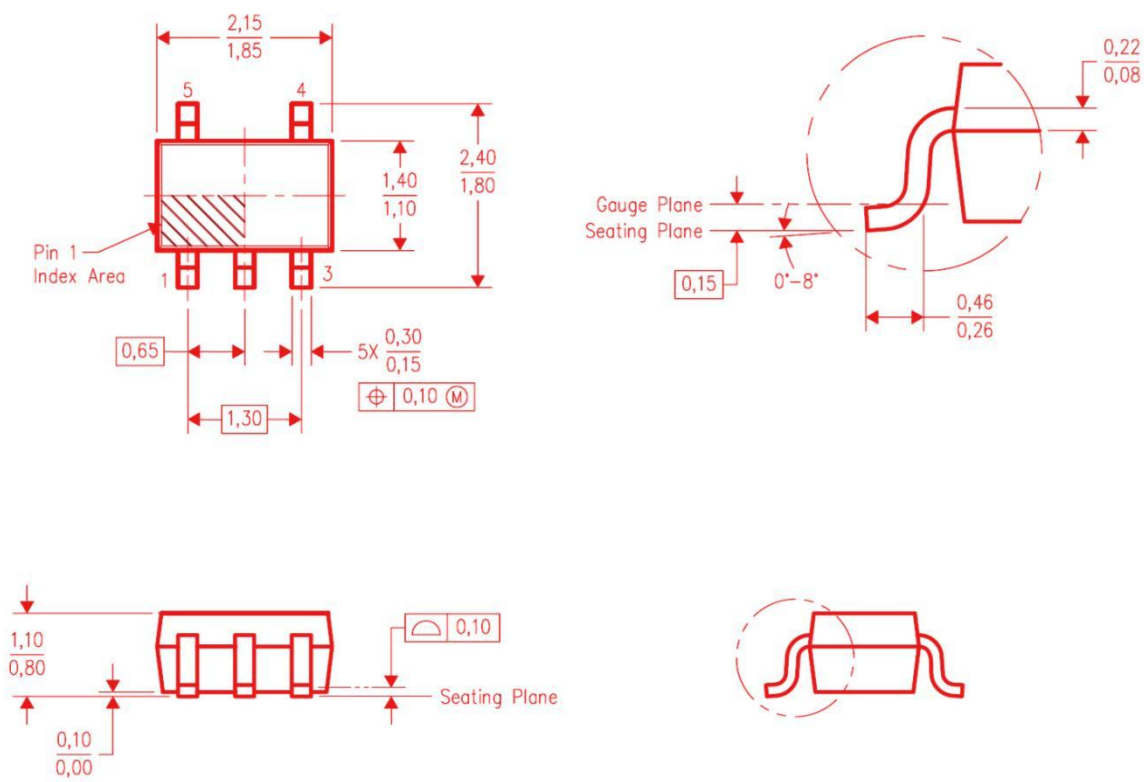
DBV (SOT-23-5)



卷轴规格

P/N	PKG	QTY
SN74LVC1G14DBVR-MS	SOT-23-5	3000

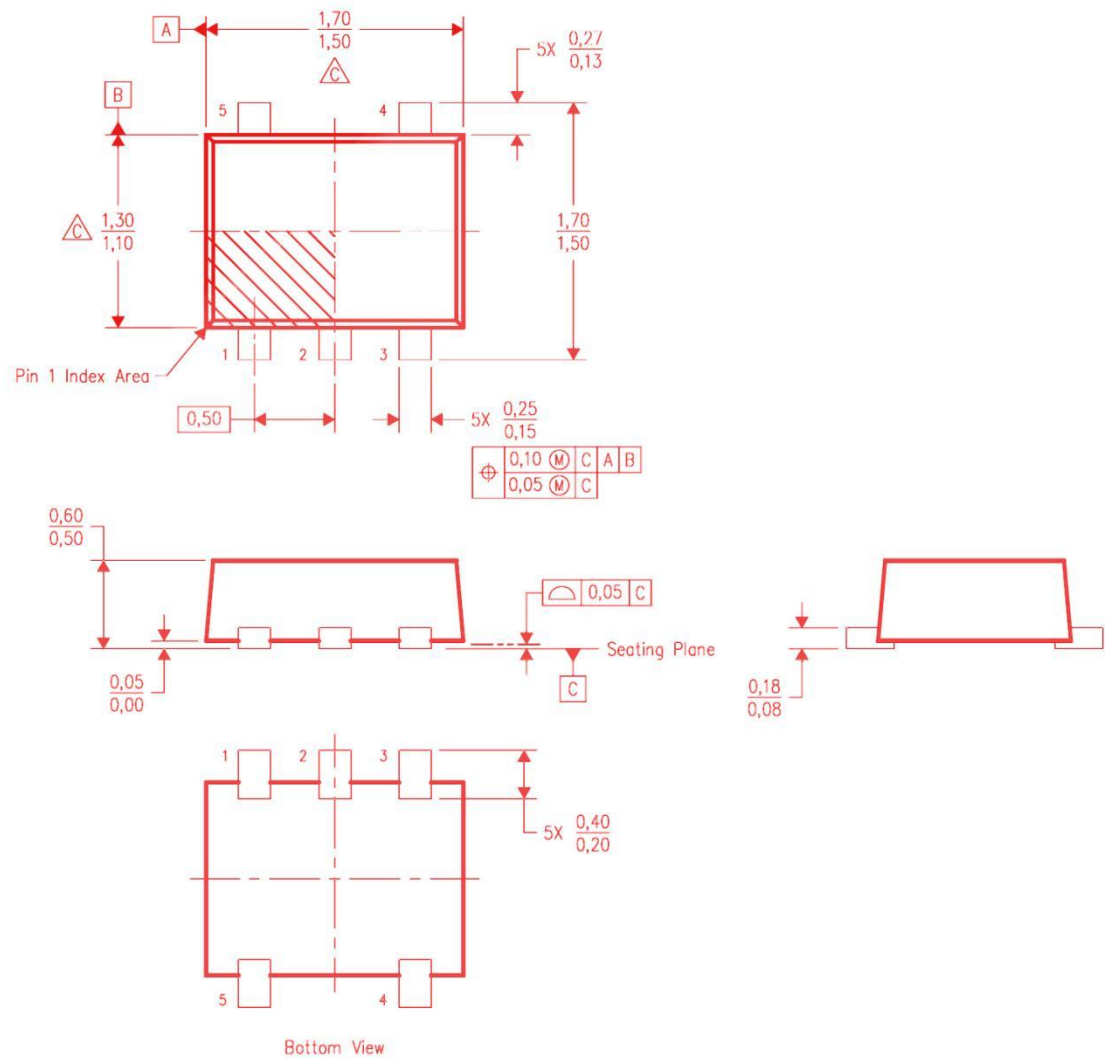
DCK (SC70-5)



卷轴规格

P/N	PKG	QTY
SN74LVC1G14DCKR-MS	SC70-5	3000

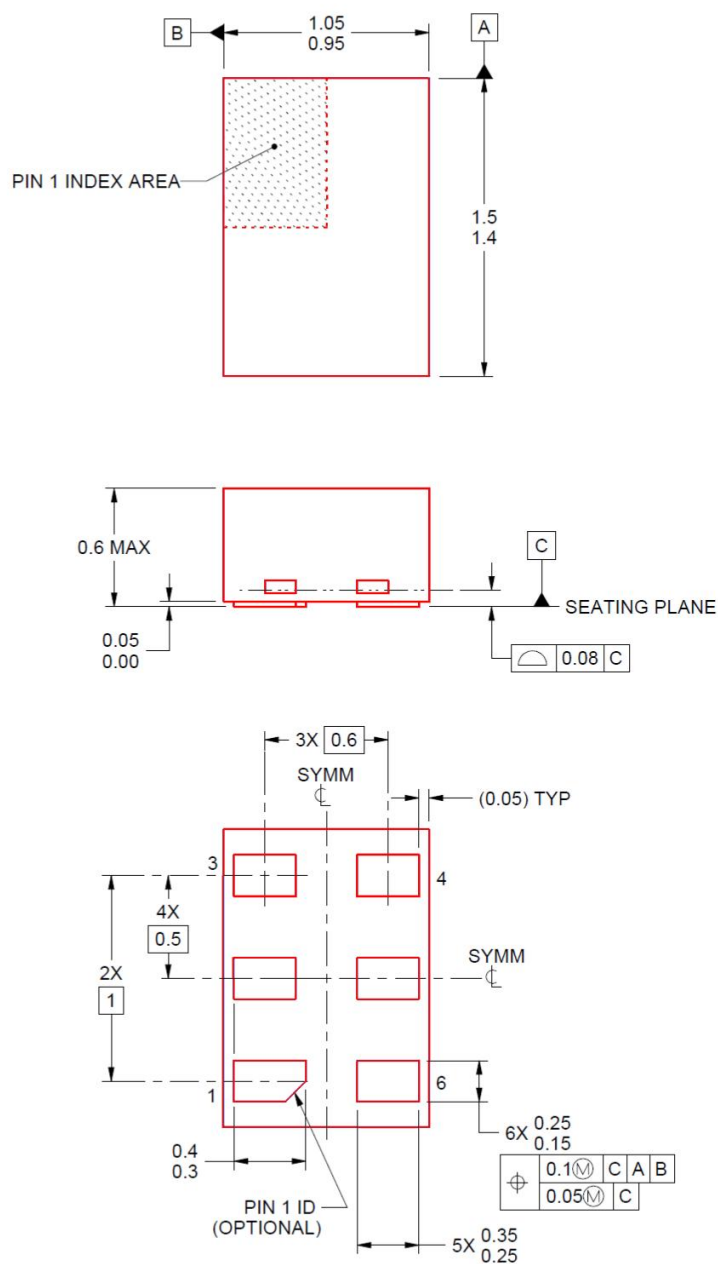
DRL (SOT-553)



卷轴规格

P/N	PKG	QTY
SN74LVC1G14DBLR-MS	SOT-553	4000

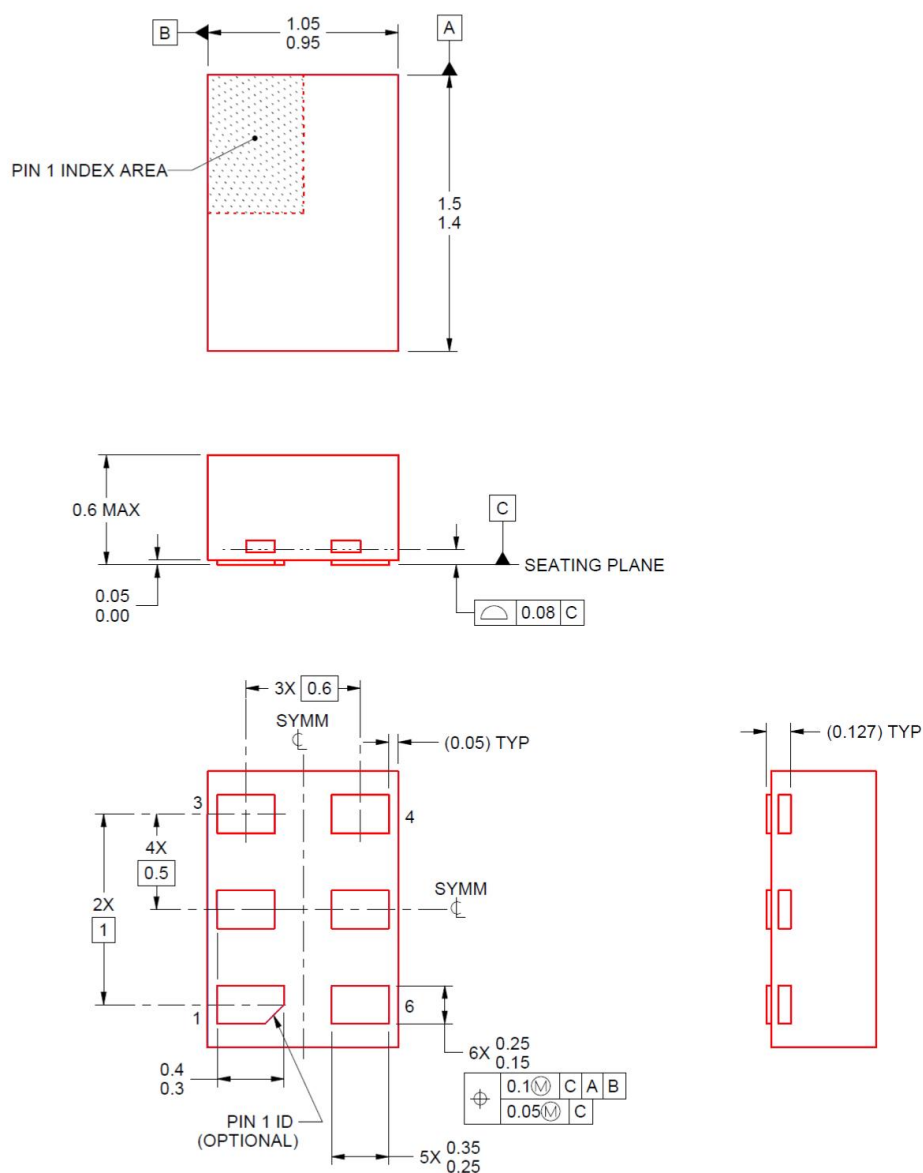
DRY (S0T-886)



卷轴规格

P/N	PKG	QTY
SN74LVC1G14DBYR-MS	SOT-886	5000

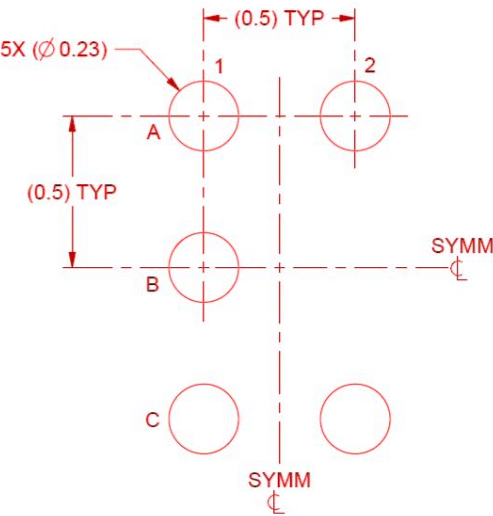
DSF (SON-6)



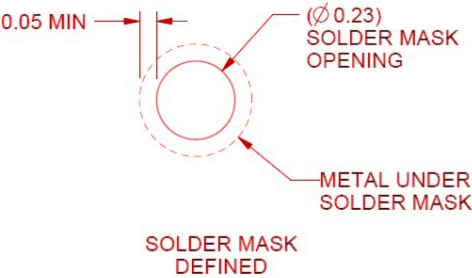
卷轴规格

P/N	PKG	QTY
SN74LVC1G14DSFR-MS	SON-6	5000

YZP (DSBGA-5)



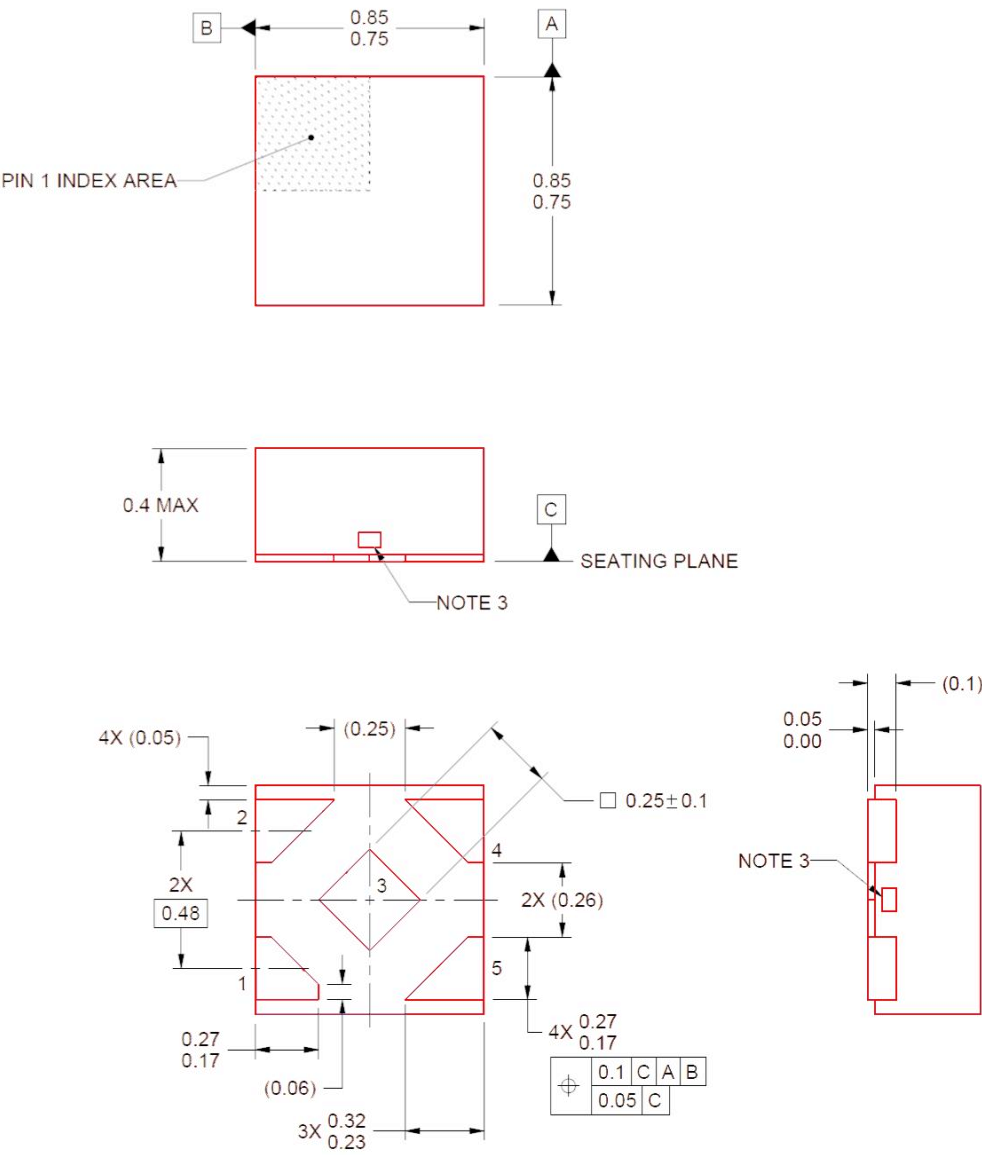
LAND PATTERN EXAMPLE
SCALE:40X



卷轴规格

P/N	PKG	QTY
SN74LVC1G14YZPR-MS	X2SON-5	3000

DPW (X2SON-5)



卷轴规格

P/N	PKG	QTY
SN74LVC1G14DPWR-MS	DSBGA-5	5000

Attention

■ Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.

■ MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specification of any and all MSKSEMI Semiconductor products described or contained herein.

■ Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

■ MSKSEMI Semiconductor strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

■ In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.

■ Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringement of intellectual property rights or other rights of third parties.

■ Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the MSKSEMI Semiconductor product that you intend to use.